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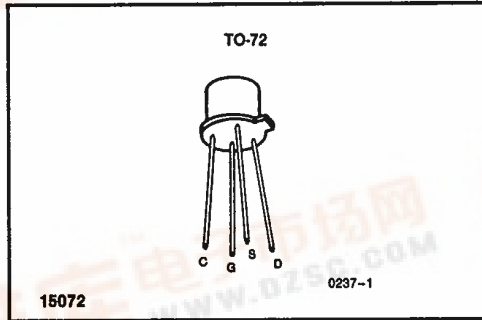
Diode Protected P-Channel Enhancement Mode MOSFET General Purpose Amplifier/Switch



FEATURES

- Channel Cut Off With Zero Gate Voltage
- Square-Law Transfer Characteristic Reduces Distortion
- Independent Substrate Connection Provides Flexibility in Biasing
- Internally Connected Diode Protects Gate From Damage Due to Overvoltage

PIN CONFIGURATION



ABSOLUTE MAXIMUM RATINGS

(T_A = 25°C unless otherwise noted)

Drain-Source or Drain-Gate Voltage	40V
Drain Current	50mA
Gate Forward Current	10μA
Gate Reverse Current	1mA
Storage Temperature	-65°C to +200°C
Operating Temperature	-55°C to +150°C
Lead Temperature (Soldering, 10sec)	+300°C
Power Dissipation	375mW
Derate above 25°C	3.0mW/°C

NOTE: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ORDERING INFORMATION

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ELECTRICAL CHARACTERISTICS (T_A = 25°C and V_{BS} = 0 unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Max	Units	
I _{GSS} F	Forward Gate-Terminal Current	V _{GS} = -25V, V _{DS} = 0 T _A = +100°C		-100	pA	
BV _{GSS}	Forward Gate-Source Break-down Voltage	I _G = -0.1mA, V _{DS} = 0	-25		V	
I _{DSS}	Zero-Gate-Voltage Drain Current	V _{DS} = -15V, V _{GS} = 0 V _{DS} = -25V, V _{GS} = 0		-10	nA	
V _{GS(th)}	Gate-Source Threshold Voltage	V _{DS} = -15V, I _D = -10μA	-1.5	-5	V	
V _{GS}	Gate-Source Voltage	V _{DS} = -15V, I _D = -8mA	-4.5	-8		
I _{D(on)}	On-State Drain Current (Note 2)	V _{DS} = -15V, V _{GS} = -15V	-40	-120	mA	
Y _{fs}	Small-Signal Common-Source Forward Transfer Admittance	V _{DS} = -15V, I _D = -8mA	f = 1kHz	3500	6500	μs
Y _{os}	Small-Signal Common-Source Output Admittance				250	
C _{iss}	Common-Source Short-Circuit Input Capacitance (Note 1)	f = 1MHz		10	pF	
C _{rss}	Common-Source Short Circuit Reverse Transfer Capacitance (Note 1)			4		

NOTE 1: For design reference only, not 100% tested.
NOTE 2: Pulse test duration 300 μs; duty cycle ≤ 3%

INTERASIL'S SOLE AND EXCLUSIVE WARRANTY OBLIGATION WITH RESPECT TO THIS PRODUCT SHALL BE THAT STATED IN THE WARRANTY ARTICLE OF THE CONDITION OF SALE. THE WARRANTY SHALL BE EXCLUSIVE AND SHALL BE IN LIEU OF ALL OTHER WARRANTIES, EXPRESS, IMPLIED OR STATUTORY, INCLUDING THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR USE.

NOTE: All typical values have been characterized but are not tested.

